

November 2013

FQPF33N10

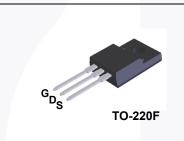
N-Channel QFET[®] MOSFET 100 V, 18 A, 52 mΩ

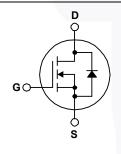
Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- 18 A, 100 V, $R_{DS(on)}$ = 52 m Ω (Max.) @ V_{GS} = 10 V, I_{D} = 9 A
- Low Gate Charge (Typ. 38 nC)
- Low Crss (Typ. 62 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating





Absolute Maximum Ratings T_c = 25°C unless otherwise noted.

Symbol	Parameter		FQPF33N10	Unit
V _{DSS}	Drain-Source Voltage		100	V
I _D	Drain Current - Continuous (T _C = 25°C	C)	18	A
	- Continuous (T _C = 100°	C)	12.7	А
I _{DM}	Drain Current - Pulsed	(Note 1)	72	А
V _{GSS}	Gate-Source Voltage		± 25	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	430	mJ
I _{AR}	Avalanche Current	(Note 1)	18	A
E _{AR}	Repetitive Avalanche Energy	(Note 1)	4.1	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	6.0	V/ns
P _D	Power Dissipation ($T_C = 25^{\circ}C$)		41	W
	- Derate above 25°C		0.27	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C
TL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 seconds		300	°C

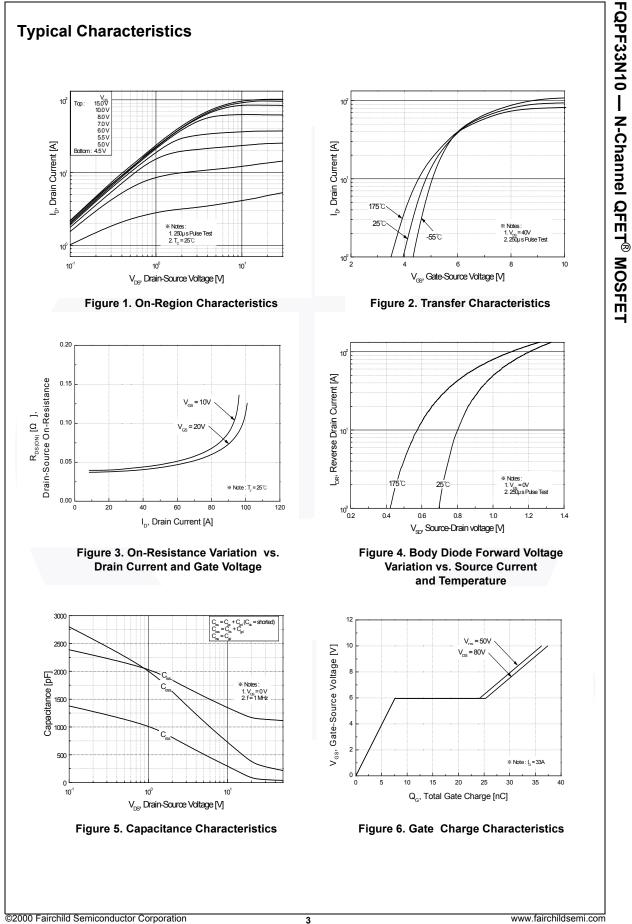
Thermal Characteristics

Symbol	Parameter	FQPF33N10	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	3.70	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W	

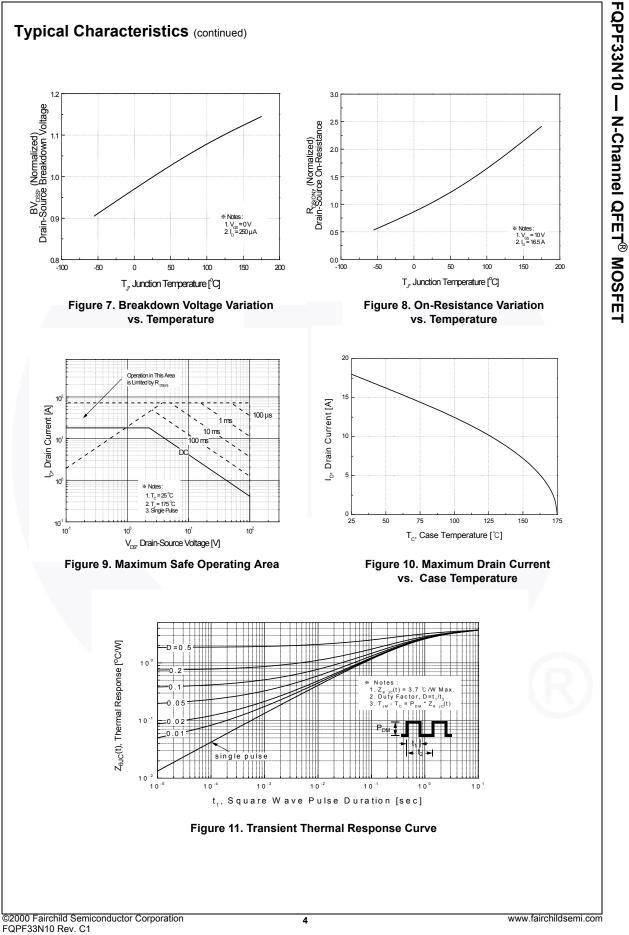
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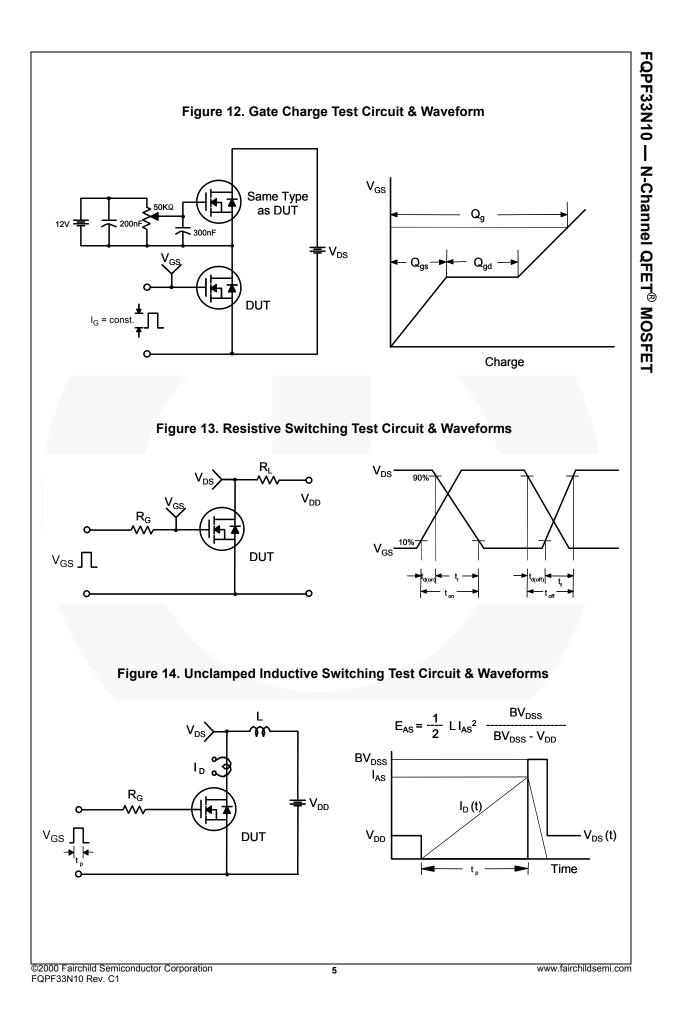
Part NumberTop MarkPackageFQPF33N10FQPF33N10TO-220F		Packing Method	Reel Size	Tape Width		th Q	Quantity		
		TO-220F				N/A	5	50 units	
lectric	cal Cl	naracteristics	T _C = 25°C	unless otherwise noted.					
Symbol		Parameter		Test Condit	ions	Min	Тур	Max	Unit
~ ~ ~ ~									
Off Cha				$y_{1} = 0 y_{1} = 0 0 0$. A	400		1	
BV _{DSS}	Drain-Source Breakdown Voltage			V _{GS} = 0 V, I _D = 250 μA		100			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient		ature	$I_D = 250 \ \mu A$, Referenced to $25^{\circ}C$			0.11		V/°C
DSS	Zero G	ate Voltage Drain Cu	rrent	V _{DS} = 100 V, V _{GS} = 0 V				1	μA
				V _{DS} = 80 V, T _C = 150°C				10	μA
I _{GSSF}		Body Leakage Curren		$V_{GS} = 25 V, V_{DS} = 0 V$				100	nA
GSSR	Gate-E	Body Leakage Curren	t, Reverse	V_{GS} = -25 V, V_{DS} = 0) V			-100	nA
On Cha	racter	istics							
V _{GS(th)}	Gate T	hreshold Voltage		$V_{DS} = V_{GS}, I_D = 250$	μA	2.0		4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance			$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 9 \text{ A}$			0.040	0.052	Ω
9 _{FS}	Forwa	rd Transconductance		V _{DS} = 40 V, I _D = 9 A			20		S
Dynami	ic Cha	racteristics							
C _{iss}		Capacitance		$V_{DS} = 25 V, V_{GS} = 0$	V		1150	1500	pF
C _{oss}	Output	Capacitance		$v_{\rm DS} = 23$ v, $v_{\rm GS} = 0$ v, f = 1.0 MHz			320	420	pF
C _{rss}	Revers	se Transfer Capacitar	nce				62	80	pF
Switchi	na Ch	aracteristics							
d(on)		n Delay Time		$V_{DD} = 50 \text{ V}, \text{ I}_{D} = 33 \text{ A},$			15	40	ns
t _r		n Rise Time					195	400	ns
t _{d(off)}	Turn-C	off Delay Time		R _G = 25 Ω			80	170	ns
f	Turn-C	off Fall Time		(Note 4)			110	230	ns
Q _g	Total G	Bate Charge		V _{DS} = 80 V, I _D = 33 Å	۹.		38	51	nC
Q _{gs}	Gate-S	Source Charge		V _{GS} = 10 V	,		7.5		nC
Q _{gd}	Gate-D	Drain Charge		00	(Note 4)		18		nC
	ource	Diode Characte	ristics an	d Maximum Rati	inas				
I _S	1	um Continuous Drain						18	Α
I _{SM}		um Pulsed Drain-Sou						72	A
V _{SD}		Source Diode Forwar		V _{GS} = 0 V, I _S = 18 A				1.5	V
t _{rr}		se Recovery Time	Ū	$V_{GS} = 0 V, I_S = 33 A,$			80		ns
Q _{rr}		se Recovery Charge		dl _F / dt = 100 A/µs			0.22		μC
otes: Repetitive R		e width limited by maximum $T_{DD} = 25 \text{ V}, R_{G} = 25 \Omega, startiD A/µs, V_{DD} ≤ B VDSS, start$	n_{α} T = 25°C	ture.			1	1	

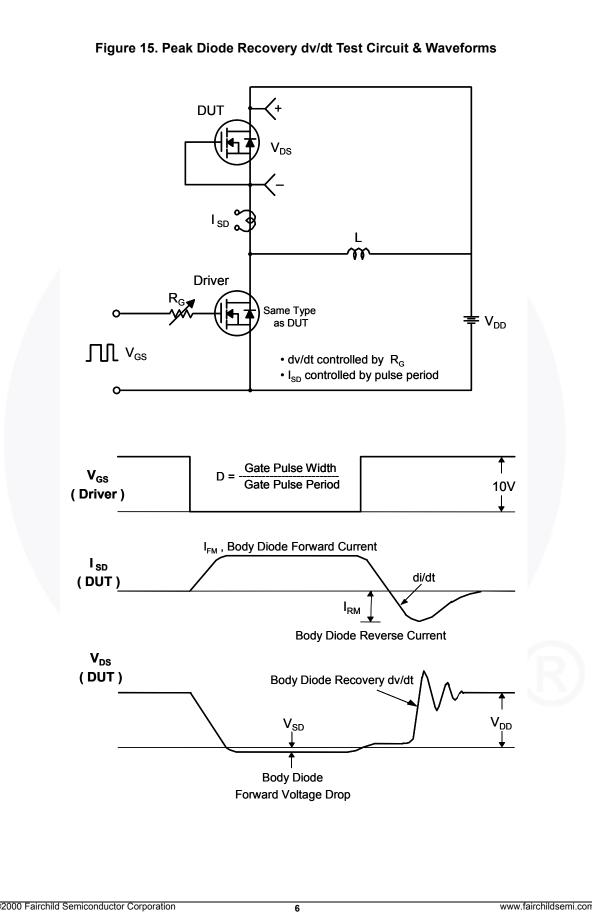
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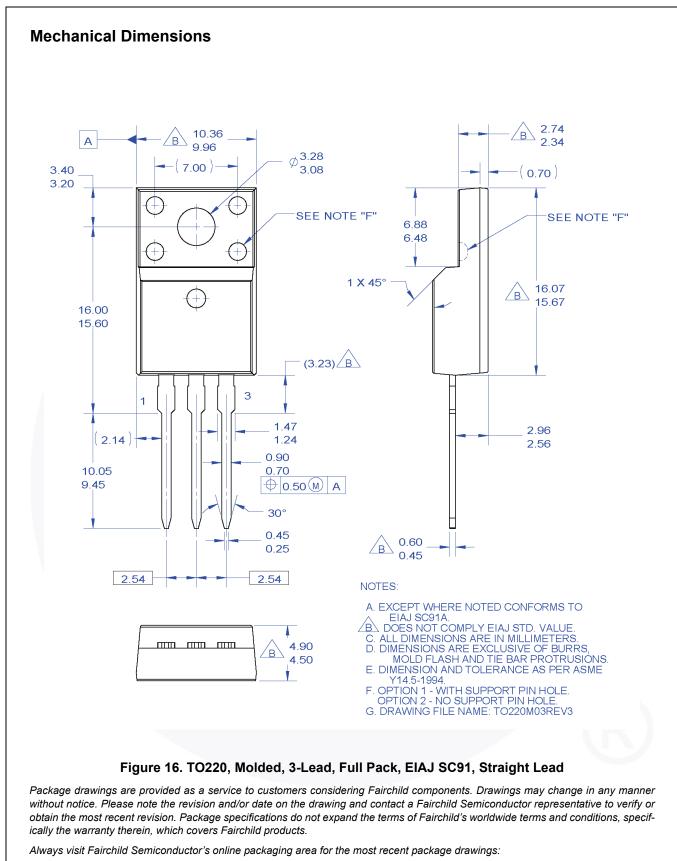
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FQPF33N10 — N-Channel QFET[®] MOSFET



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